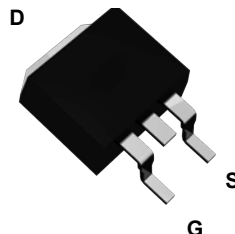
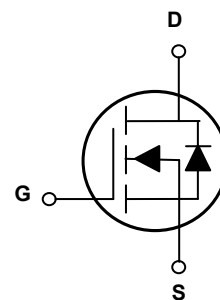


Main Product Characteristics

V_{DS}	60V
$R_{DS(ON)}$	4.0m Ω
I_D	150A



TO-263 (D²PAK)



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFT06150 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	150	A
Drain Current-Continuous($T_C=100^{\circ}\text{C}$)	$I_{D(100^{\circ}\text{C})}$	105	A
Pulsed Drain Current	I_{DM}	600	A
Maximum Power Dissipation	P_D	220	W
Derating Factor		1.47	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy ⁵	E_{AS}	900	mJ
Thermal Resistance, Junction-to-Case ²	$R_{\theta JC}$	0.68	$^{\circ}\text{C}/\text{W}$
Operating Junction Temperature Range	T_J	-55 To +175	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 To +175	$^{\circ}\text{C}$

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=75A$	-	3.1	4.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=75A$	-	80	-	S
Dynamic Characteristics⁴						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, F=1.0MHz$	-	5451	-	PF
Output Capacitance	C_{oss}		-	609	-	
Reverse Transfer Capacitance	C_{rss}		-	488	-	
Switching Characteristics⁴						
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=75A, V_{GS}=10V$	-	130.8	-	nC
Gate-Source Charge	Q_{gs}		-	22.8	-	
Gate-Drain Charge	Q_{gd}		-	56.9	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=30V, R_L=0.4\Omega, V_{GS}=10V, R_G=2.5\Omega$	-	25	-	nS
Turn-On Rise Time	t_r		-	23	-	
Turn-Off Delay Time	$t_{d(off)}$		-	90	-	
Turn-Off Fall Time	t_f		-	38	-	
Drain-Source Diode Characteristics						
Diode Forward Current ²	I_S		-	-	150	A
Diode Forward Voltage ³	V_{SD}	$I_S=75A, V_{GS}=0V$	-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J=25^\circ\text{C}, I_F=75A, di/dt=-100A/\mu s^3$	-	60	-	nS
Reverse Recovery Charge	Q_{rr}		-	80	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on is negligible(turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, L=0.5mH, R_G=25\Omega$

Typical Electrical and Thermal Characteristic Curves

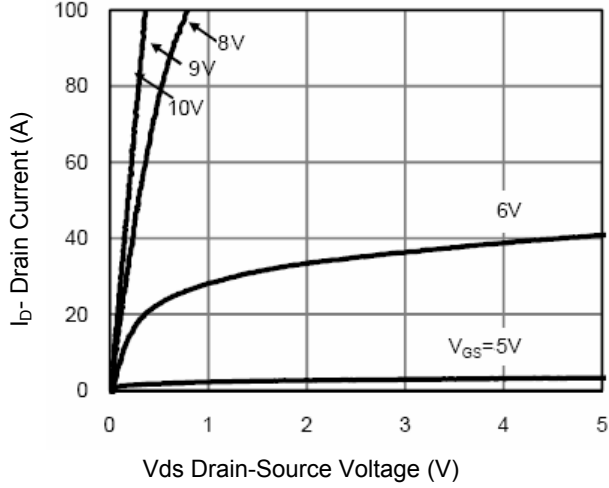


Figure 1. Output Characteristics

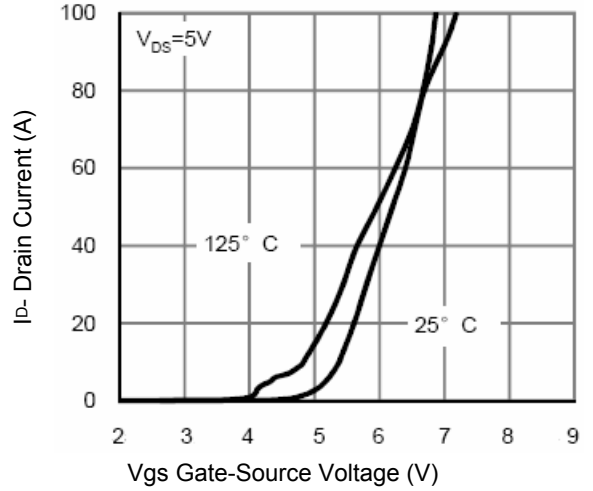


Figure 2. Transfer Characteristics

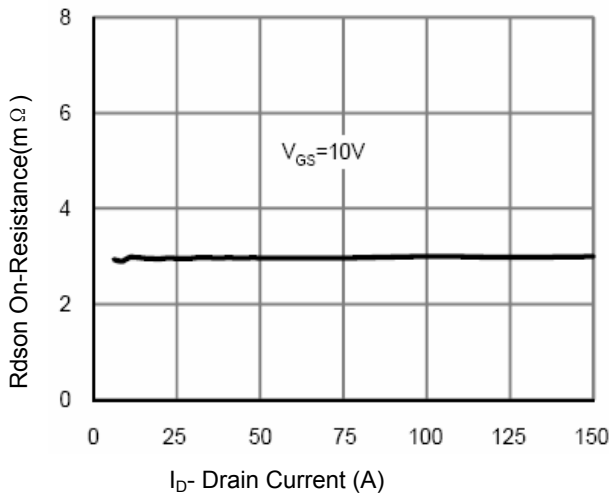


Figure 3. Rdson- Drain Current

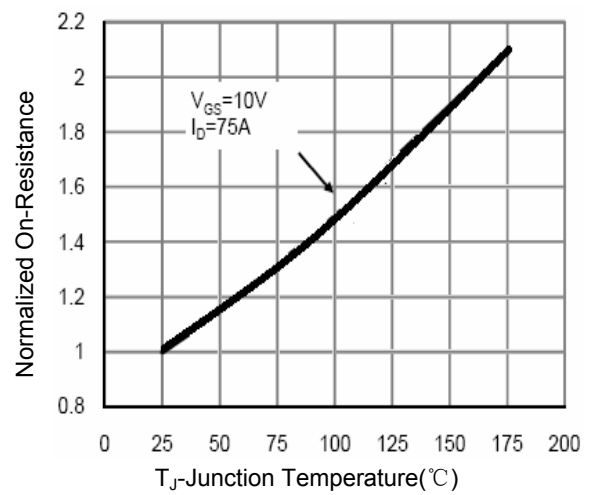


Figure 4. Rdson-Junction Temperature

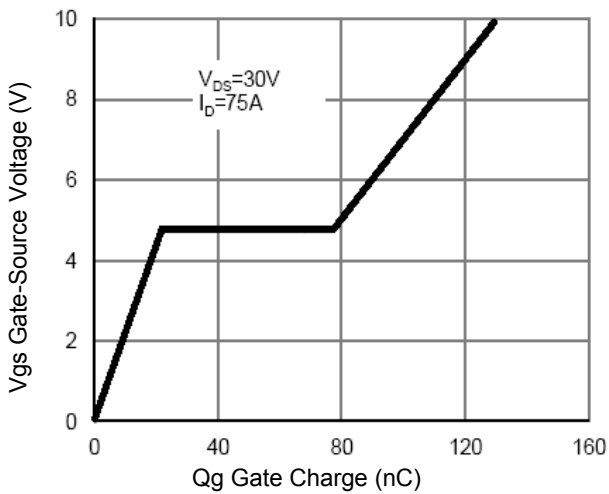


Figure 5. Gate Charge

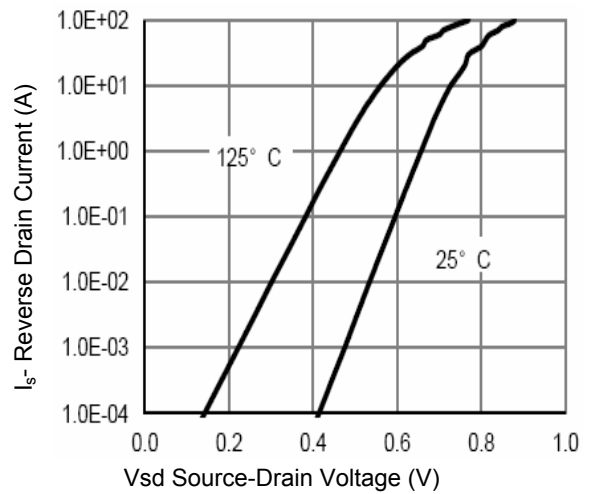


Figure 6. Source- Drain Diode Forward

Typical Electrical and Thermal Characteristic Curves

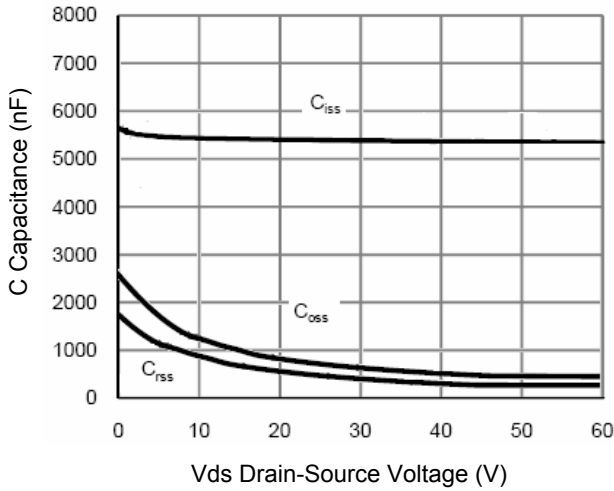


Figure 7. Capacitance vs Vds

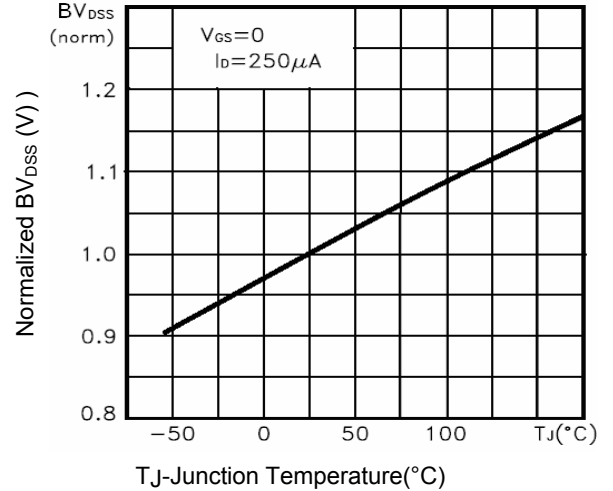


Figure 8. BV_{DSS} vs Junction Temperature

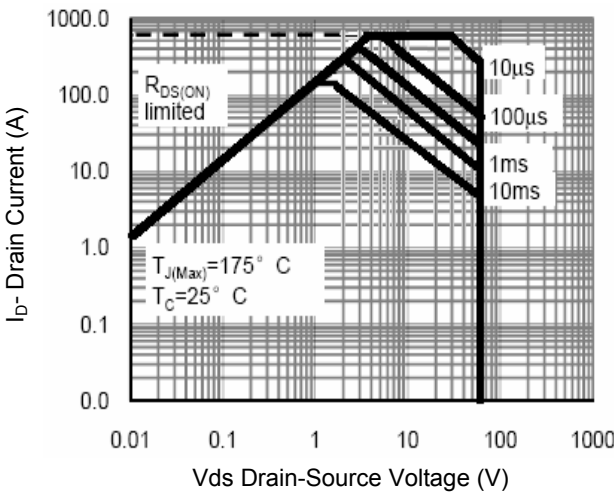


Figure 9. Safe Operation Area

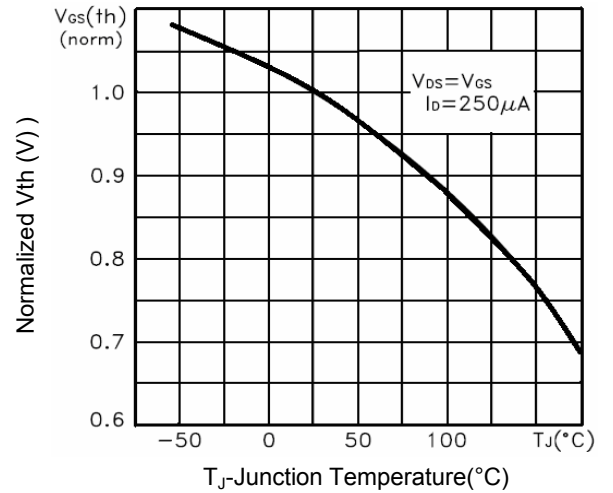


Figure 10. V_{th} vs Junction Temperature

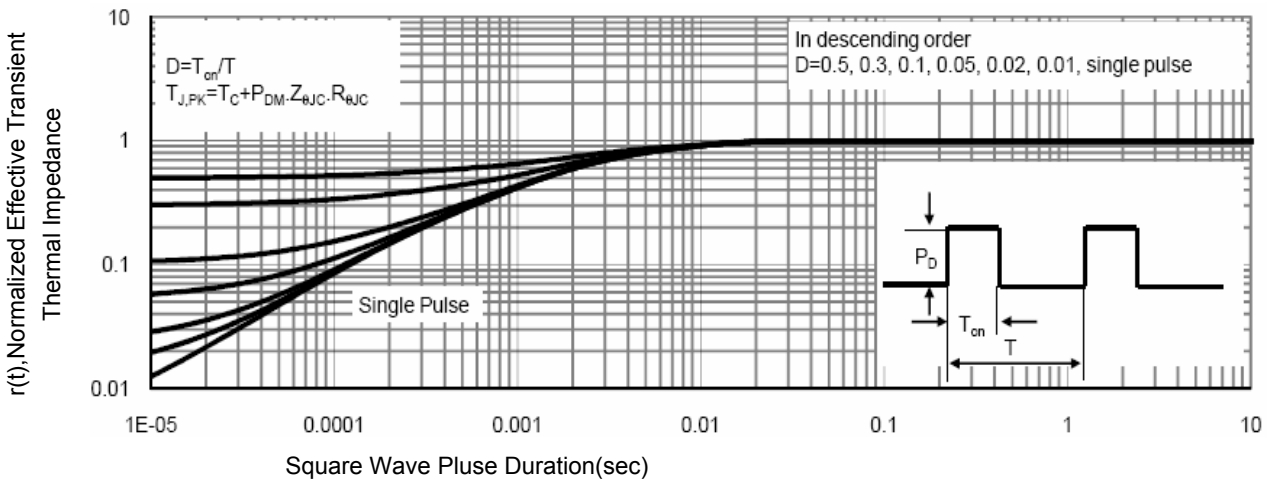


Figure 11. Normalized Maximum Transient Thermal Impedance

Typical Electrical and Thermal Characteristic Curves

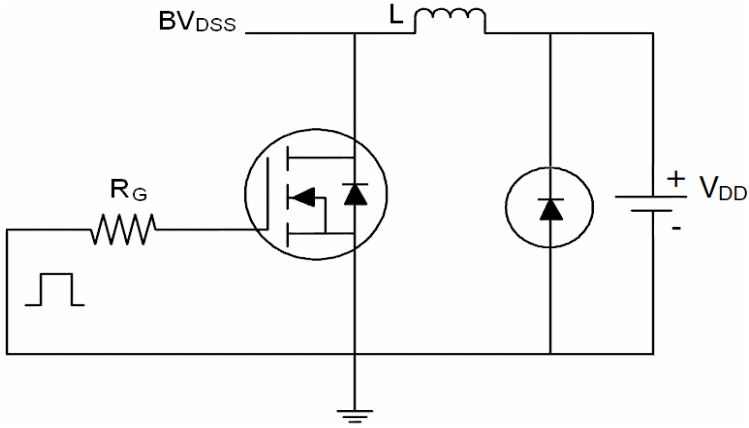


Figure 12. E_{AS} Test Circuit

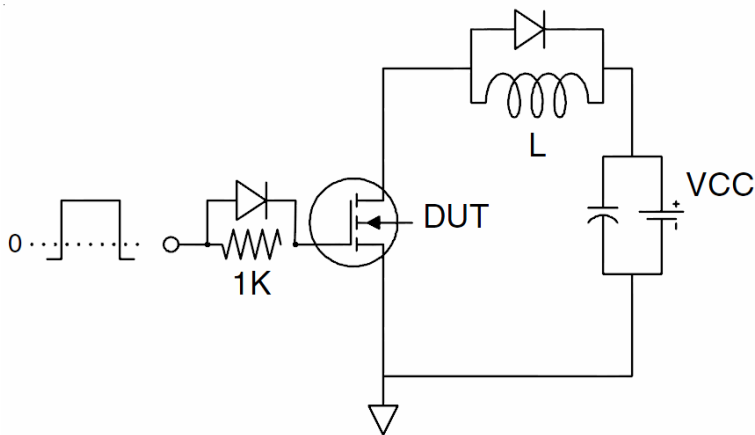


Figure 13. Gate Charge Test Circuit

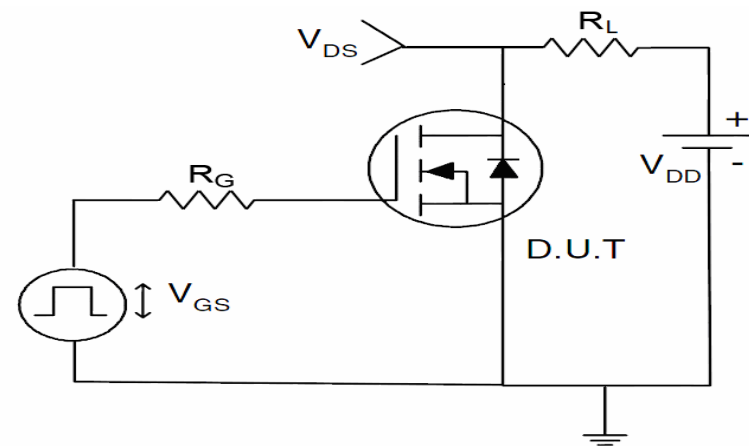
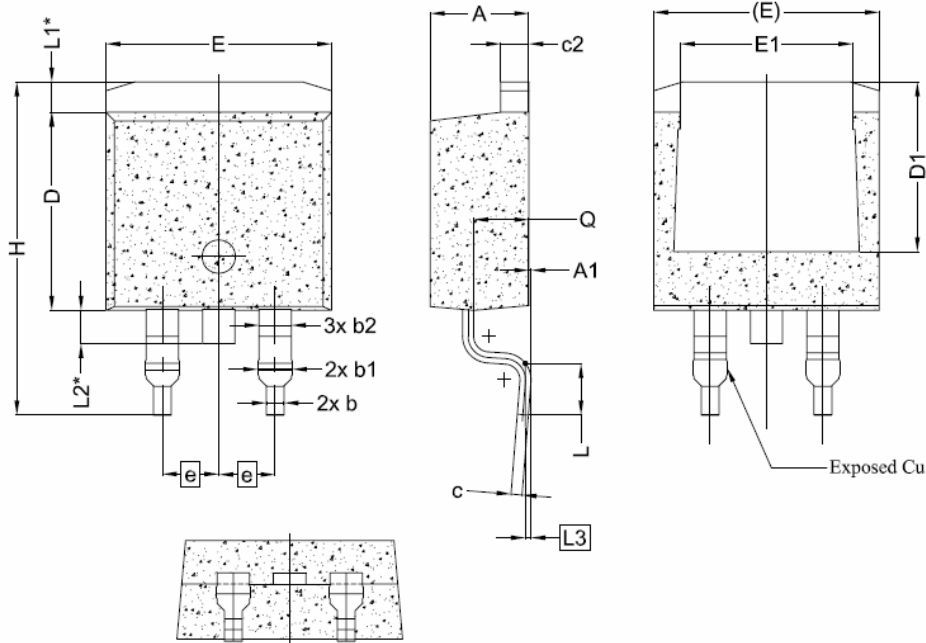


Figure 14. Switch Time Test Circuit

Package Outline Dimensions (TO-263/D²PAK)



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	-
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54BS		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70